HFZT

2SD602A

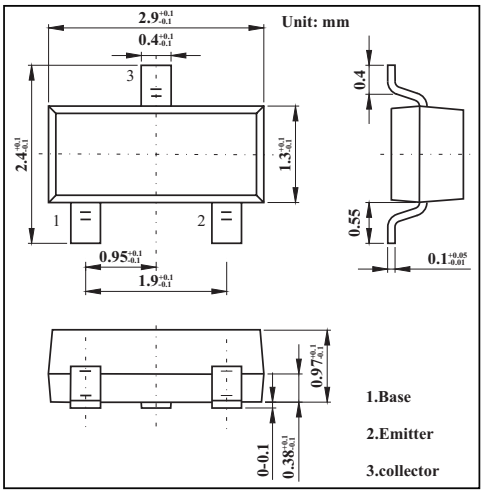
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Low collector to emitter saturation voltage
- General purpose amplifier applications
- PNP Transistor

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

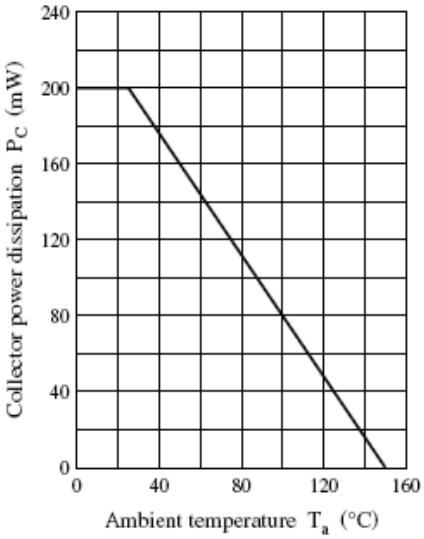
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Peak collector current	I_{CP}	1	A
Collector power Dissipation	P_C	200	mW
Junction and Storage Temperature	Tj,Tstg	-55 to +150	℃

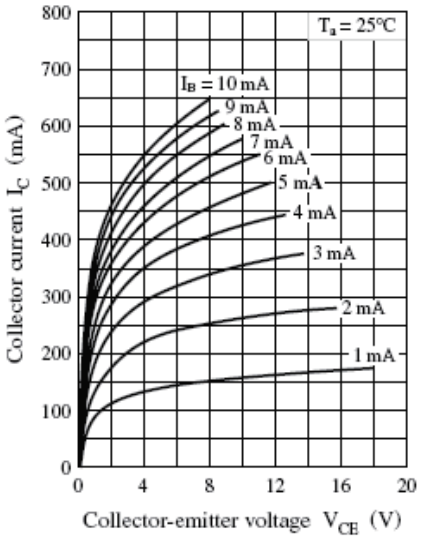
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V,I_E=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=10V,I_C=150mA	85		340	
		V_{CE}=10V,I_C=500mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=300mA, I_B=30mA		0.35	0.6	V
Transition frequency	f_T	V_{CB}=10V, I_E= -50mA, f=200MHz		200		MHz
Output capacitance	C_{ob}	V_{CB}=10V, I_E=0,f=1MHz		6	15	pF

RATINGS AND CHARACTERISTIC CURVES

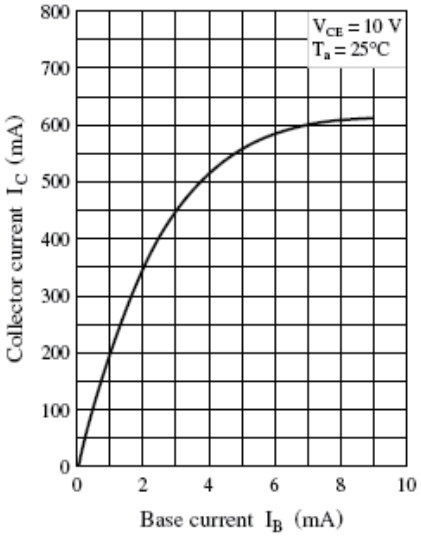
P_C — T_a



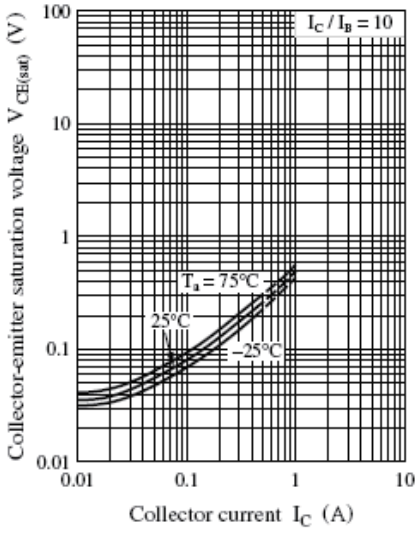
I_C — V_{CE}



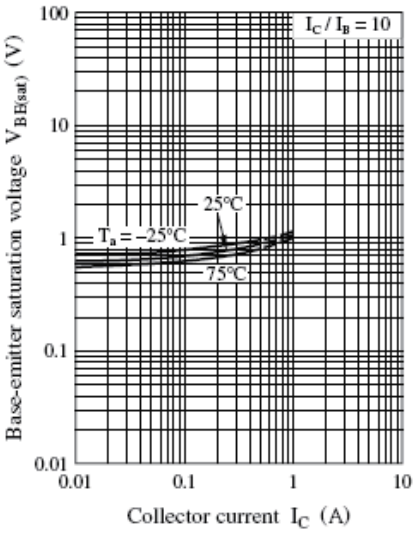
I_C — I_B



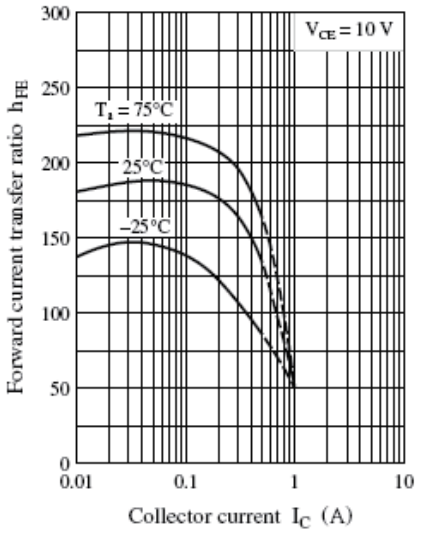
$V_{CE(sat)}$ — I_C



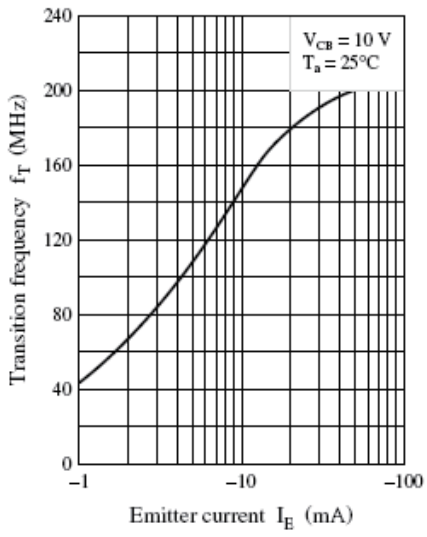
$V_{BE(sat)}$ — I_C



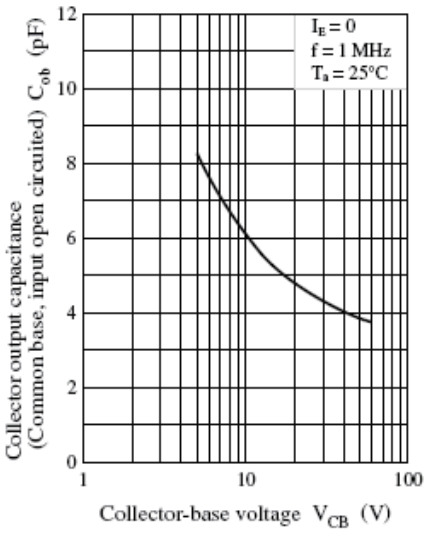
h_{FE} — I_C



f_T — I_E



C_{ob} — V_{CB}



V_{CER} — R_{BE}